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DERWENT-WEEK: 200251

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TITLE: Nitride semiconductor device and  
manufacturing method  
thereof

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PATENT-FAMILY:

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ABSTRACTED-PUB-NO: KR2002000898A

BASIC-ABSTRACT:

NOVELTY - A method for manufacturing a nitride semiconductor device is provided to easily grow an indium-containing compound layer like an  $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$  layer, by growing  $\text{In}_x\text{Ga}_{1-x}\text{N}$  as a buffer layer so that mole density of indium is easily increased or decreased.

DETAILED DESCRIPTION - The buffer layer(12) is stacked on a substrate(11). A semiconductor layer group including at least a semiconductor layer is stacked on the buffer layer, wherein the buffer layer includes an indium-containing nitride. A nitride semiconductor device includes the substrate, the buffer layer and the semiconductor layer.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: NITRIDE SEMICONDUCTOR DEVICE  
MANUFACTURE METHOD

DERWENT-CLASS: L03 U11 U12

CPI-CODES: L04-A02B1; L04-A02C1;

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제2 상부 클래드층 P형 $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ ( $0 < x < 1, 0 < y < 1$ )	17
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